

## N-Channel 20-V (D-S) MOSFET

| PRODUCT SUMMARY     |                                  |                                 |                       |  |  |  |
|---------------------|----------------------------------|---------------------------------|-----------------------|--|--|--|
| V <sub>DS</sub> (V) | $R_{DS(on)}(\Omega)$             | I <sub>D</sub> (A) <sup>a</sup> | Q <sub>g</sub> (Typ.) |  |  |  |
| 20                  | 0.015 at V <sub>GS</sub> = 4.5 V | 9.1                             | 29 nC                 |  |  |  |
| 20                  | 0.013 at V <sub>GS</sub> = 10 V  | 9.7                             | 29110                 |  |  |  |

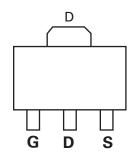
#### **FEATURES**

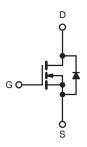
DT-Trench Power MOSFET



#### **APPLICATIONS**

· Load Switches for Portable Devices





N-Channel MOSFET

| Parameter Drain-Source Voltage Gate-Source Voltage |  | Symbol           | Limit                              | Unit |  |
|--|--|------------------|------------------------------------|------|--|
|  |  | V <sub>DS</sub>  | 20                                 | V    |  |
|  |  | V <sub>GS</sub>  | ± 12                               |      |  |
|  | $T_C = 25 ^{\circ}\text{C}$<br>$T_C = 70 ^{\circ}\text{C}$                     |                  | 9.7 <sup>a</sup><br>8 <sup>a</sup> |      |  |
| Continuous Drain Current (T <sub>J</sub> = 150 °C) | T <sub>A</sub> = 25 °C   | I <sub>D</sub>   | 8.7 <sup>a, b, c</sup>             |      |  |
| T <sub>A</sub> = 70 °C  Pulsed Drain Current       |  | I <sub>DM</sub>  | 7 <sup>a, b, c</sup>               | A    |  |
| Continuous Source-Drain Diode Current              | $T_C = 25 ^{\circ}C$<br>$T_A = 25 ^{\circ}C$                                   | - I <sub>S</sub> | 7.2<br>6.1 <sup>b, c</sup>         |      |  |
|  | T <sub>C</sub> = 25 °C   |                  | 6.3                                |      |  |
| Maximum Power Dissipation                          | $T_C = 70  ^{\circ}C$<br>$T_A = 25  ^{\circ}C$                                 | P <sub>D</sub>   | 4<br>2.5 <sup>b, c</sup>           | w    |  |
|  | T <sub>A</sub> = 70 °C   |                  | 1.6 <sup>b</sup> , c               |      |  |
| Operating Junction and Storage Temperatur          | ating Junction and Storage Temperature Range T <sub>J</sub> , T <sub>stg</sub> |                  | - 55 to 150                        | °C   |  |
| Soldering Recommendations (Peak Tempera            | ature) <sup>e, f</sup>   |                  | 260                                |      |  |

| THERMAL RESISTANCE RATINGS                     |              |                   |         |         |        |  |
|--|--------------|-------------------|---------|---------|--------|--|
| Parameter                                      |              | Symbol            | Typical | Maximum | Unit   |  |
| Maximum Junction-to-Ambient <sup>a, c, d</sup> | t ≤ 5 s      | R <sub>thJA</sub> | 40      | 50      | °C/W   |  |
| Maximum Junction-to-Foot (Drain)               | Steady State | $R_{thJF}$        | 15      | 20      | 7 0,00 |  |

- a. Package limited, T<sub>C</sub> = 25 °C.
  b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under Steady State conditions is 95 °C/W.
- e. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.



| Parameter  | Symbol                    | Test Conditions   | Min.           | Тур.  | Max.  | Unit  |
|--|---------------------------|---|----------------|-------|-------|-------|
| Static   | <u>.</u>                  |   |                | 1     |       | ı     |
| Drain-Source Breakdown Voltage                     | V <sub>DS</sub>           | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$   | 20             |       |       | V     |
| V <sub>DS</sub> Temperature Coefficient            | $\Delta V_{DS}/T_{J}$     | J 250 A   |                | 25    |       | mV/°C |
| V <sub>GS(th)</sub> Temperature Coefficient        | $\Delta V_{GS(th)}/T_{J}$ | $I_D = 250  \mu A$  |                | - 4.0 |       |       |
| Gate-Source Threshold Voltage                      | V <sub>GS(th)</sub>       | $V_{DS} = V_{GS}$ , $I_D = 250 \mu A$   | 0.5            |       | 1.0   | V     |
| Gate-Source Leakage                                | I <sub>GSS</sub>          | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$                                     |                |       | ± 100 | nA    |
| Zara Oata Valta va Daria Oamani                    | I <sub>DSS</sub>          | $V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$   |                |       | 1     |       |
| Zero Gate Voltage Drain Current                    |                           | V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C                 |                |       | 10    | μΑ    |
| On-State Drain Current <sup>a</sup>                | I <sub>D(on)</sub>        | $V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$                                      | 30             |       |       | Α     |
|  |                           | $V_{GS} = 4.5 \text{ V}, I_D = 6.3 \text{ A}$   | 0.015<br>0.013 |       |       | Ω     |
| Drain-Source On-State Resistance <sup>a</sup>      | R <sub>DS(on)</sub>       | $V_{GS} = 10 \text{ V}, I_D = 4.5 \text{ A}$  |                |       |       |       |
| Forward Transconductance <sup>a</sup>              | 9 <sub>fs</sub>           | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 6.3 A  |                | 45    |       | S     |
| Dynamic <sup>b</sup>                               |                           |   |                |       |       | I     |
| Input Capacitance                                  | C <sub>iss</sub>          |   |                | 810   |       | pF    |
| Output Capacitance                                 | C <sub>oss</sub>          | $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$                      |                | 120   |       |       |
| Reverse Transfer Capacitance                       | C <sub>rss</sub>          |   |                | 100   |       |       |
| Total Gate Charge                                  | Qg                        | $V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 6.3 \text{ A}$                 |                | 22    | 33    | nC    |
|  |                           |   |                | 10    | 15    |       |
| Gate-Source Charge                                 | $Q_{gs}$                  | $V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 6.3 \text{ A}$                |                | 2.5   |       |       |
| Gate-Drain Charge                                  | $Q_{gd}$                  |   |                | 1.7   |       |       |
| Gate Resistance                                    | $R_g$                     | f = 1 MHz   |                | 2.4   |       | Ω     |
| Turn-on Delay Time                                 | t <sub>d(on)</sub>        |   |                | 15    | 25    |       |
| Rise Time  | t <sub>r</sub>            | $V_{DD}$ = 10 V, $R_L$ = 1.5 $\Omega$   |                | 10    | 15    | ns    |
| Turn-Off Delay Time                                | t <sub>d(off)</sub>       | $I_D\cong 6.7~A,~V_{GEN}=4.5~V,~R_g=1~\Omega$   |                | 35    | 55    |       |
| Fall Time  | t <sub>f</sub>            |   |                | 12    | 20    |       |
| Turn-on Delay Time                                 | t <sub>d(on)</sub>        |   |                | 10    | 15    |       |
| Rise Time  | t <sub>r</sub>            | $V_{DD}$ = 10 V, $R_L$ = 1.5 $\Omega$   |                | 12    | 20    |       |
| Turn-Off Delay Time                                | t <sub>d(off)</sub>       | $I_D\cong 6.7$ A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$                                |                | 25    | 40    |       |
| Fall Time  | t <sub>f</sub>            |   |                | 10    | 15    |       |
| <b>Drain-Source Body Diode Characteristic</b>      | s                         |   |                |       |       |       |
| Continuous Source-Drain Diode Current              | I <sub>S</sub>            | $T_C = 25  ^{\circ}C$   |                |       | 7.2   | ۸     |
| Pulse Diode Forward Current                        | I <sub>SM</sub>           |   |                |       | 30    | Α     |
| Body Diode Voltage                                 | $V_{SD}$                  | I <sub>S</sub> = 6.7 A, V <sub>GS</sub> = 0 V   |                | 0.8   | 1.2   | V     |
| Body Diode Reverse Recovery Time                   | t <sub>rr</sub>           |   |                | 20    | 40    | ns    |
| Body Diode Reverse Recovery Charge Q <sub>rr</sub> |                           | $I_F = 6.7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$ |                | 10    | 20    | nC    |
| Reverse Recovery Fall Time                         | t <sub>a</sub>            | i <sub>F</sub> = 0.7 A, αί/αι = 100 Α/μs, 1 <sub>J</sub> = 25 °C                      |                | 10    |       | 20    |
| Reverse Recovery Rise Time                         | t <sub>b</sub>            |   |                | 10    |       | ns    |

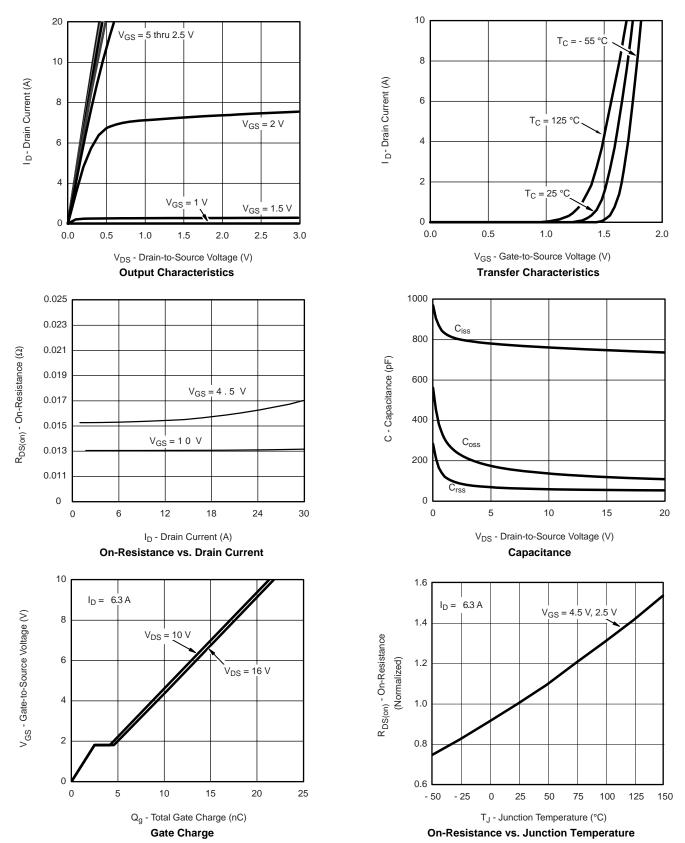
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

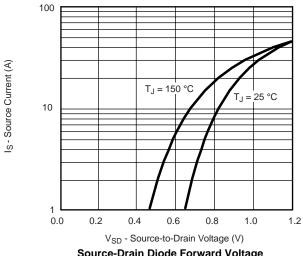


### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

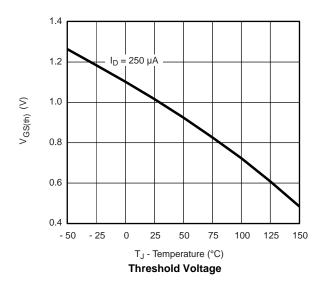


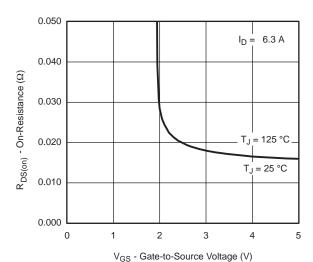


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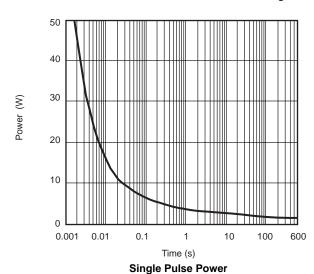


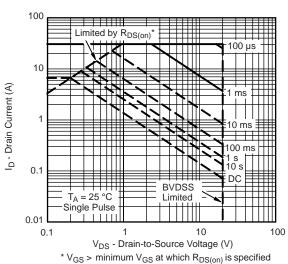
#### Source-Drain Diode Forward Voltage





On-Resistance vs. Gate-to-Source Voltage

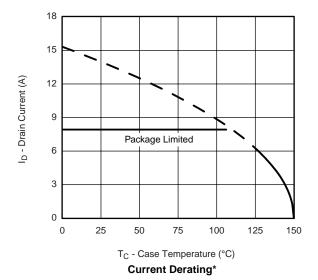


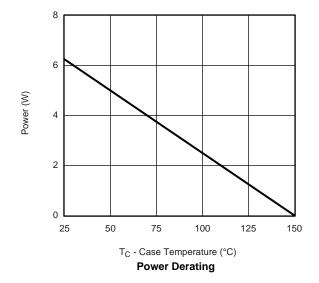


Safe Operating Area, Junction-to-Ambient



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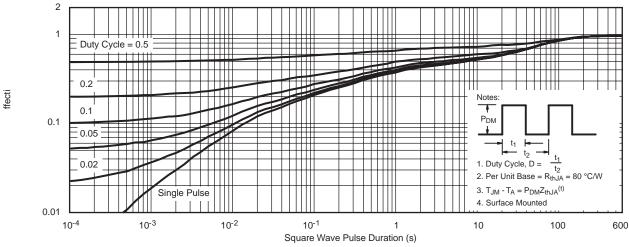




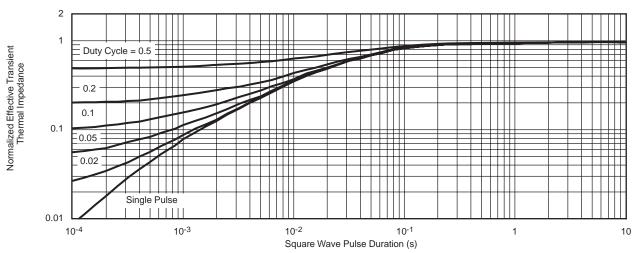
<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

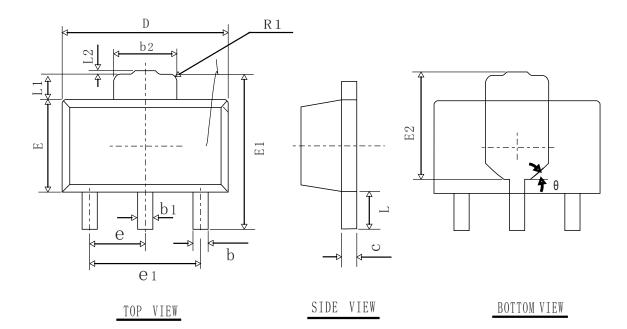


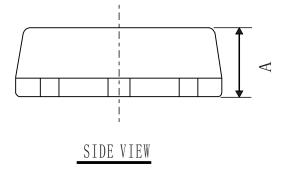
Normalized Thermal Transient Impedance, Junction-to-Foot



Din-Tek SEMICONDUCTOR

DTC2056 www.din-tek.jp





# COMMON DIMENSIONS (UNITS OF MEASURE=mm)

| SYMBOL | MIN       | NOM       | MAX  |  |  |
|--------|-----------|-----------|------|--|--|
| A      | 1.30      | 1.50      | 1.70 |  |  |
| b      | 0.30      | 0.40      | 0.53 |  |  |
| b1     | 0.40      | 0.48      | 0.62 |  |  |
| b2     | 1.55      | 1.70      | 1.85 |  |  |
| С      | 0.30      | 0.40      | 0.50 |  |  |
| D      | 4.20      | 4.50      | 4.80 |  |  |
| Е      | 2.20      | 2.50      | 2.80 |  |  |
| E1     | 3.80      | 4.20      | 4.60 |  |  |
| E2     | 2.55      | 2.85      | 3.15 |  |  |
| e 1    | 2.80      | 3.00 3.20 |      |  |  |
| L      | 0.80      | 1.00      | 1.20 |  |  |
| L1     | 0.60      | 0.70      | 0.80 |  |  |
| L2     | 0.075 REF |           |      |  |  |
| R 1    | 0.2 BSC   |           |      |  |  |
| θ      | 45° TYP   |           |      |  |  |
| е      | 1.5 BSC   |           |      |  |  |





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